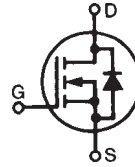


**PolarHV™ Power
MOSFET**
IXTP16N50PM

$$V_{DSS} = 500V$$

$$I_{D25} = 7.5A$$

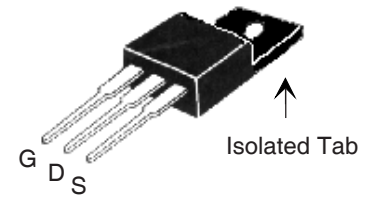
$$R_{DS(on)} \leq 420m\Omega$$

(Electrically Isolated Tab)


N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

**OVERMOLDED
(IXTP...M) OUTLINE**

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 500 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1 M\Omega$ | 500 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ C$ | 7.5 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 35 | A |
| I_A | $T_C = 25^\circ C$ | 16 | A |
| E_{AS} | $T_C = 25^\circ C$ | 750 | mJ |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J = 150^\circ C$ | 10 | V/ns |
| P_D | $T_C = 25^\circ C$ | 75 | W |
| T_J | | - 55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | - 55 ... +150 | $^\circ C$ |
| T_L | 1.6 mm (0.062 in.) from Case for 10 s | 300 | $^\circ C$ |
| T_{SOLD} | Plastic Body for 10 s | 260 | $^\circ C$ |
| M_d | Mounting Torque | 1.13/10 | Nm/lb.in. |
| Weight | | 2.5 | g |



G = Gate D = Drain
S = Source

Features

- Plastic Overmolded Tab for Electrical Isolation
- International Standard Package
- Avalanche Rated
- Fast Intrinsic Diode
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

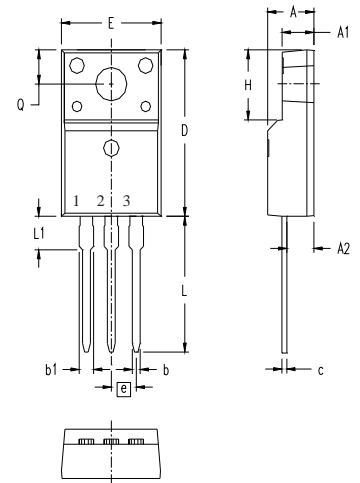
Applications

- Switched-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 250\mu A$ | 500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | 3.0 | | 5.5 V |
| I_{GSS} | $V_{GS} = \pm 30V$, $V_{DS} = 0V$ | | | ± 100 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 5 μA 50 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 8A$, Note 1 | | | 420 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{V}$, $I_D = 8\text{A}$, Note 1 | 9 | 16 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 2480 | pF |
| C_{oss} | | | 237 | pF |
| C_{rss} | | | 18 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 8\text{A}$ $R_G = 10\Omega$ (External) | | 24 | ns |
| t_r | | | 28 | ns |
| $t_{d(off)}$ | | | 70 | ns |
| t_f | | | 25 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 8\text{A}$ | | 43 | nC |
| Q_{gs} | | | 15 | nC |
| Q_{gd} | | | 12 | nC |
| R_{thJC} | | | | 1.66 $^\circ\text{C/W}$ |

ISOLATED TO-220 (IXTP...M)



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

| SYM | INCHES | | MILLIMETERS | |
|-----------------|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .177 | .193 | 4.50 | 4.90 |
| A1 | .092 | .108 | 2.34 | 2.74 |
| A2 | .101 | .117 | 2.56 | 2.96 |
| b | .028 | .035 | 0.70 | 0.90 |
| b1 | .050 | .058 | 1.27 | 1.47 |
| c | .018 | .024 | 0.45 | 0.60 |
| D | .617 | .633 | 15.67 | 16.07 |
| E | .392 | .408 | 9.96 | 10.36 |
| e | .100 BSC | | 2.54 BSC | |
| H | .255 | .271 | 6.48 | 6.88 |
| L | .499 | .523 | 12.68 | 13.28 |
| L1 | .119 | .135 | 3.03 | 3.43 |
| $\varnothing P$ | .121 | .129 | 3.08 | 3.28 |
| Q | .126 | .134 | 3.20 | 3.40 |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|-------|
| | | Min. | Typ. | Max. |
| I_s | $V_{GS} = 0\text{V}$ | | | 16 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 64 A |
| V_{SD} | $I_F = I_s$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 16\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$ | | 400 | ns |

Notes: 1. Pulse Test, $t \leq 300\mu\text{s}$; Duty Cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ 25°C

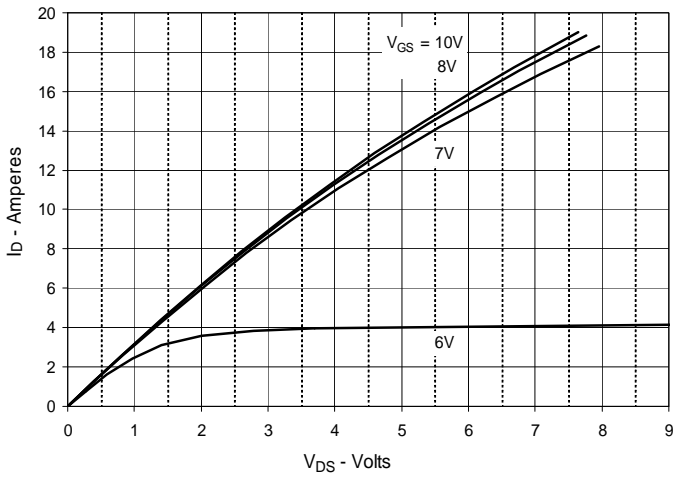


Fig. 2. Output Characteristics @ 125°C

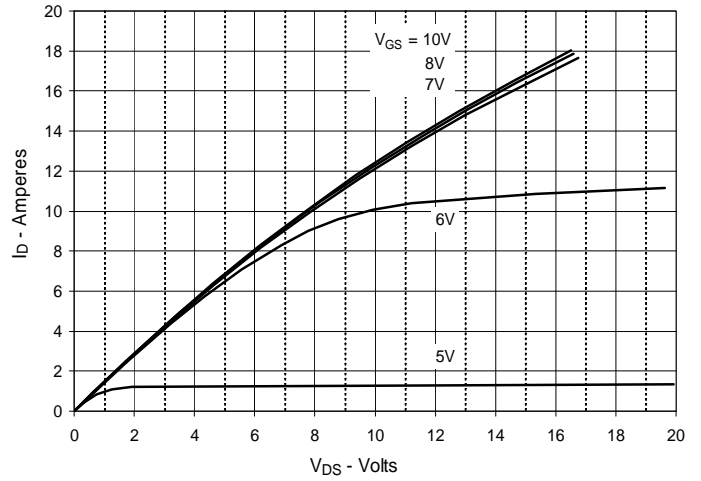


Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 8A$ Value vs. Junction Temperature

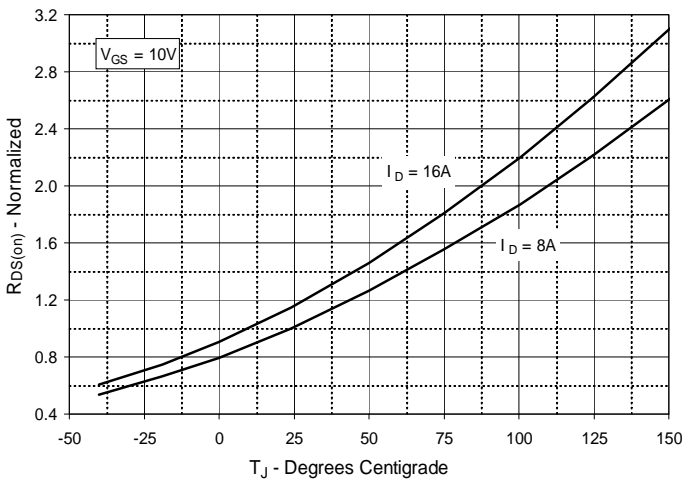


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 8A$ Value vs. Drain Current

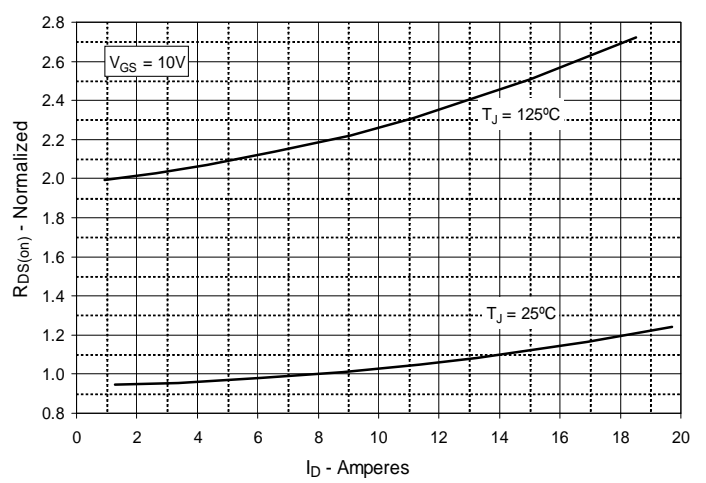


Fig. 5. Maximum Drain Current vs. Case Temperature

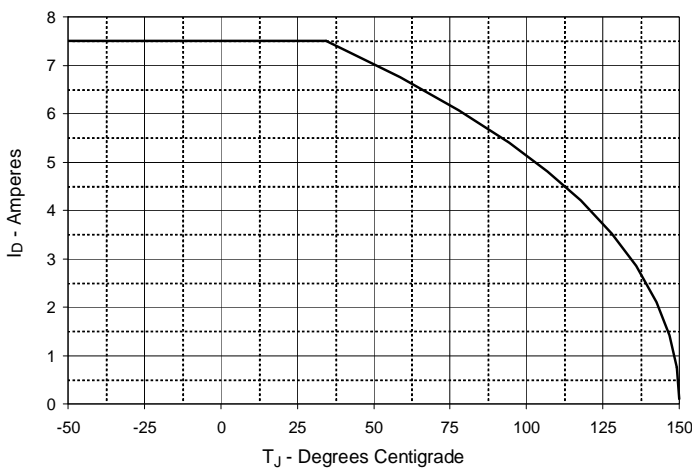


Fig. 6. Input Admittance

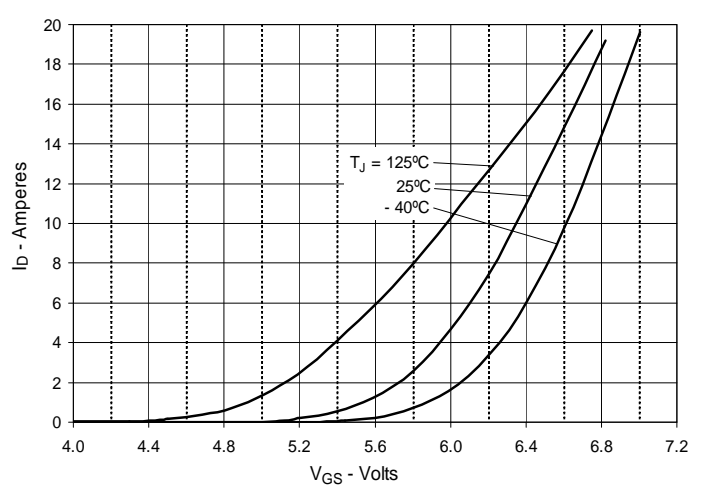


Fig. 7. Transconductance

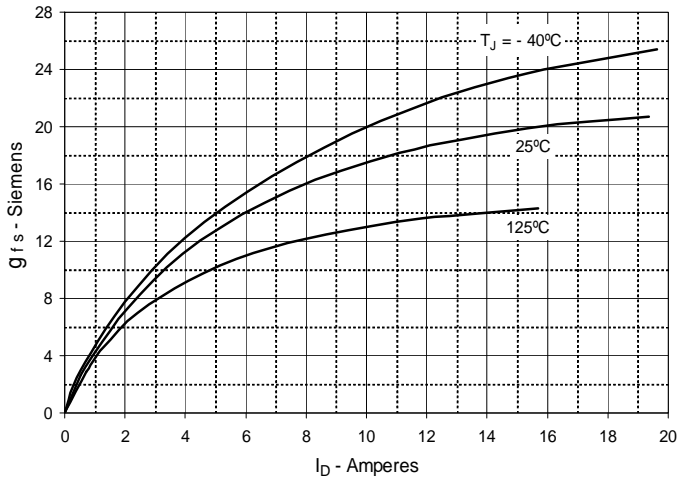


Fig. 8. Forward Voltage Drop of Intrinsic Diode

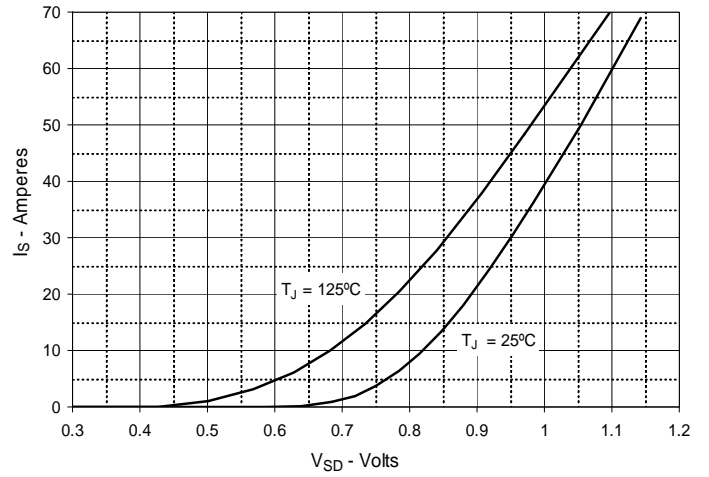


Fig. 9. Gate Charge

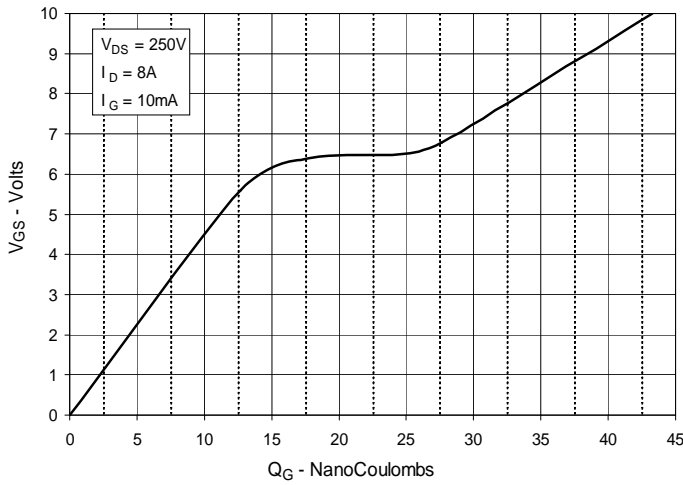


Fig. 10. Capacitance

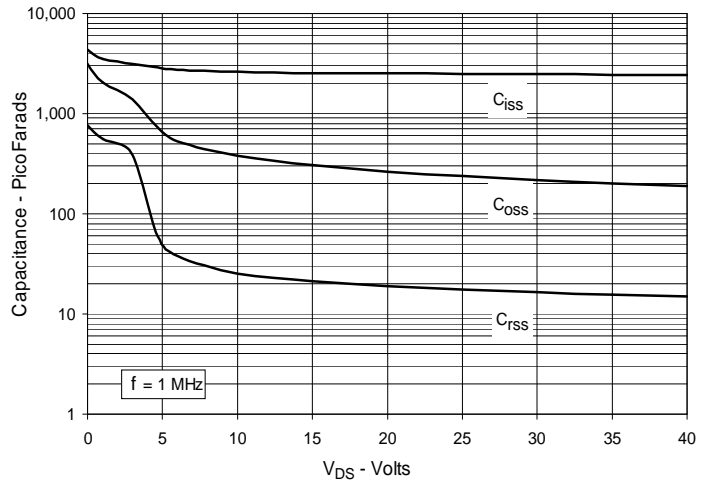


Fig. 11. Forward-Bias Safe Operating Area

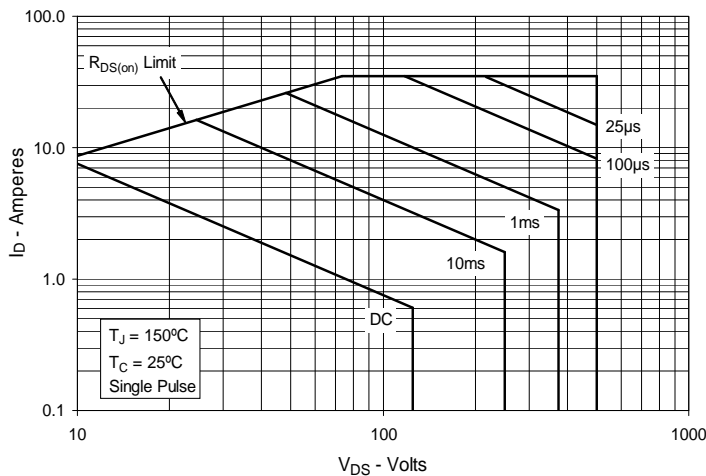
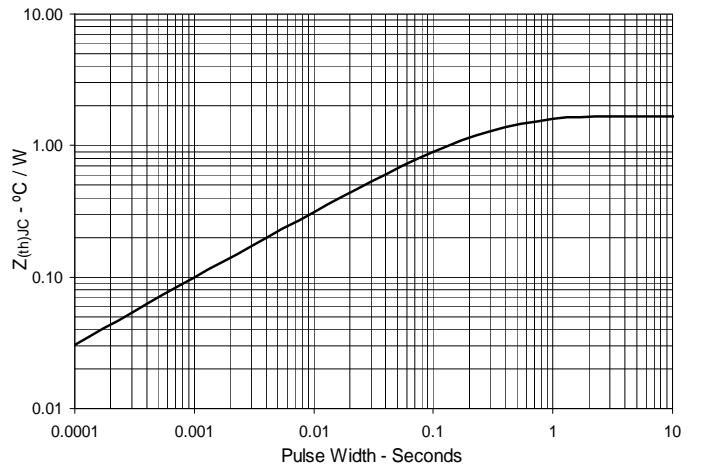


Fig. 12. Maximum Transient Thermal Impedance



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